

Description

The RST85H21 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in automotive applications and a wide variety of other applications.

General Features

- $V_{DSS} = 85V, I_D = 210A$ (Note5)

$$R_{DS(ON)} < 3.8m\Omega @ V_{GS}=10V$$

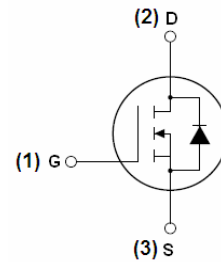
- Good stability and uniformity with high E_{AS}
- Special process technology for high ESD capability
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

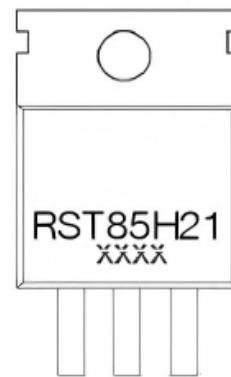
- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

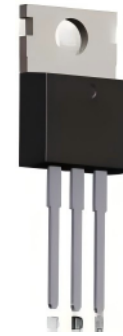
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
RST85H21	RST85H21	TO-220	-	-	-

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DSS}	85	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	210 (Note5)	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D (100^\circ C)$	150	A
Pulsed Drain Current	I_{DM}	850	A
Maximum Power Dissipation	P_D	310	W
Derating factor		2.07	W/ $^\circ C$

Single pulse avalanche energy ^(Note 3)	E_{AS}	2200	mJ
Peak Diode Recovery dv/dt ^(Note 4)	dv/dt	5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 1)	$R_{\theta JC}$	0.48	°C/W
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	85	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±200	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	3.2	3.8	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =20A	35	-	-	S
Dynamic Characteristics						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, F=1.0MHz	-	11000	-	PF
Output Capacitance	C _{OSS}		-	914	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	695	-	PF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =38V, I _D =40A V _{GS} =10V, R _{GEN} =1.2Ω ^(Note2)	-	23	-	nS
Turn-on Rise Time	t _r		-	190	-	nS
Turn-Off Delay Time	t _{d(off)}		-	130	-	nS
Turn-Off Fall Time	t _f		-	120	-	nS
Total Gate Charge	Q _g	V _{DS} =60V, I _D =40A, V _{GS} =10V ^(Note2)	-	250	-	nC
Gate-Source Charge	Q _{gs}		-	48	-	nC
Gate-Drain Charge	Q _{gd}		-	98	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =40A	-	-	1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 40A di/dt = 100A/μs ^(Note2)	-	63	-	nS
Reverse Recovery Charge	Q _{rr}		-	98	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

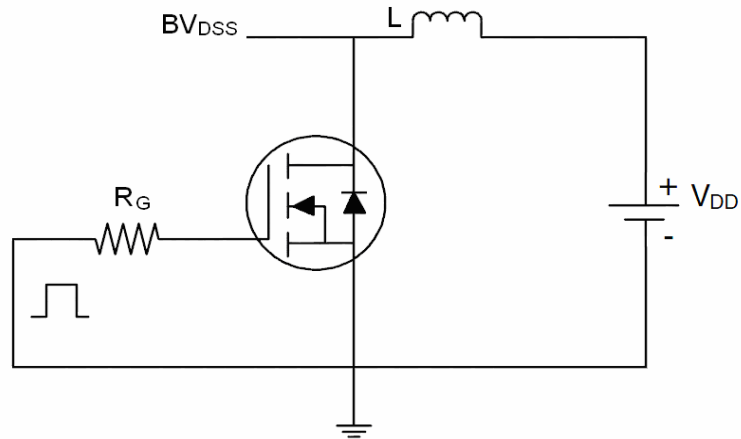
Notes:

1. Surface Mounted on FR4 Board, $t \leq 10$ sec.
2. Pulse Test: Pulse Width $\leq 400\mu s$, Duty Cycle $\leq 2\%$.
3. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=42.5V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=37A$
4. $ISD \leq 125A, di/dt \leq 260A/\mu s, V_{DD} \leq V(BR)_{DSS}, T_J \leq 175^{\circ}\text{C}$
5. Package limitation current is 190A.

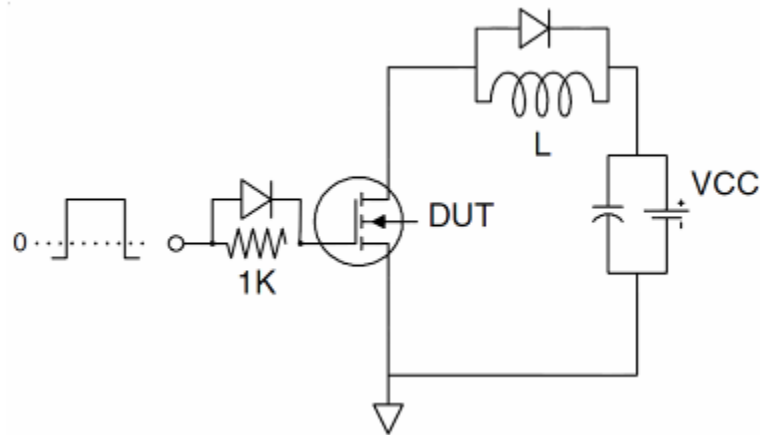
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Test Circuit

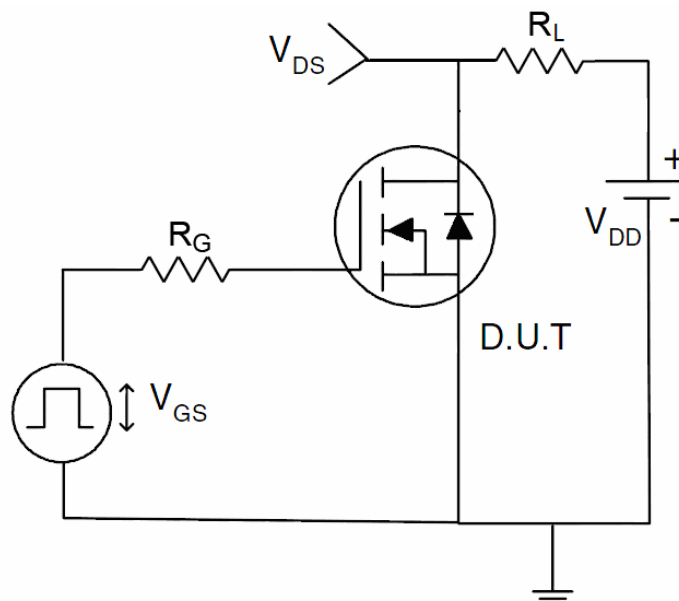
1) E_{AS} test Circuit



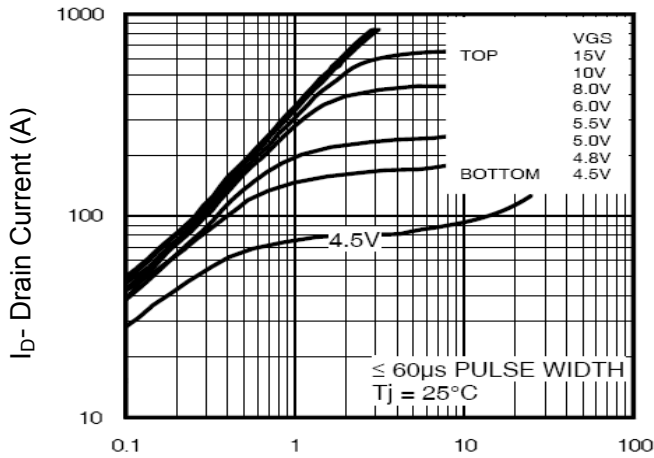
2) Gate charge test Circuit



3) Switch Time Test Circuit

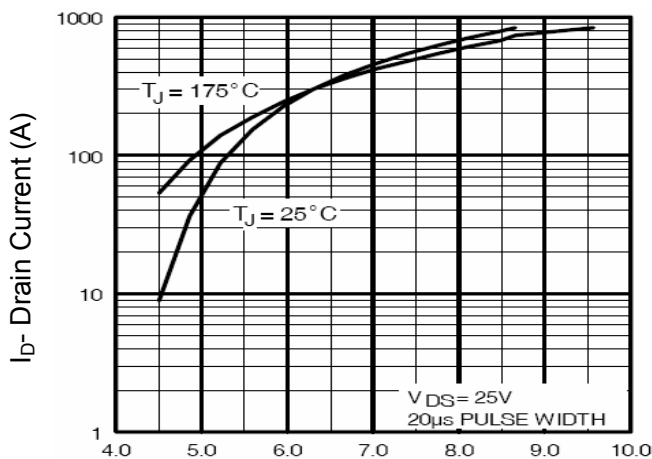


Typical Electrical and Thermal Characteristics



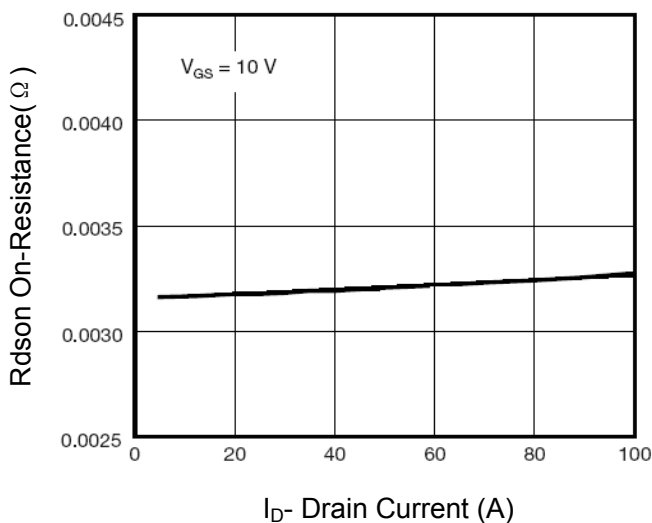
Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



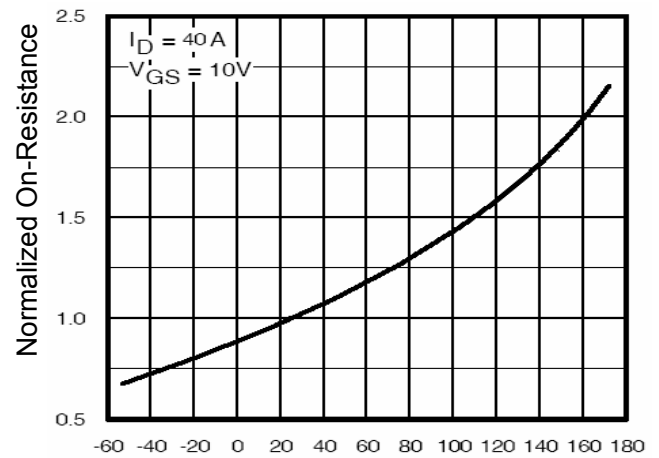
Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics



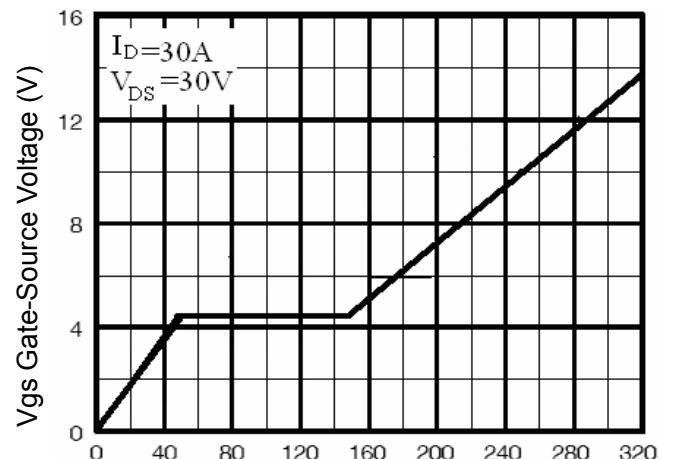
Id- Drain Current (A)

Figure 3 Rdson- Drain Current



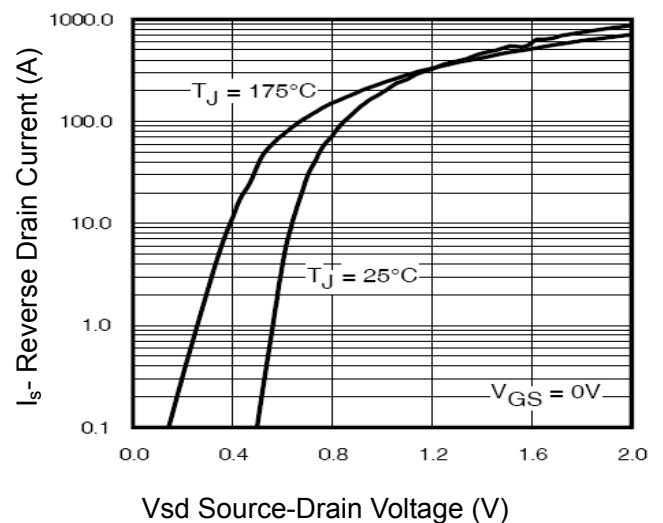
Tj-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



Qg Gate Charge (nC)

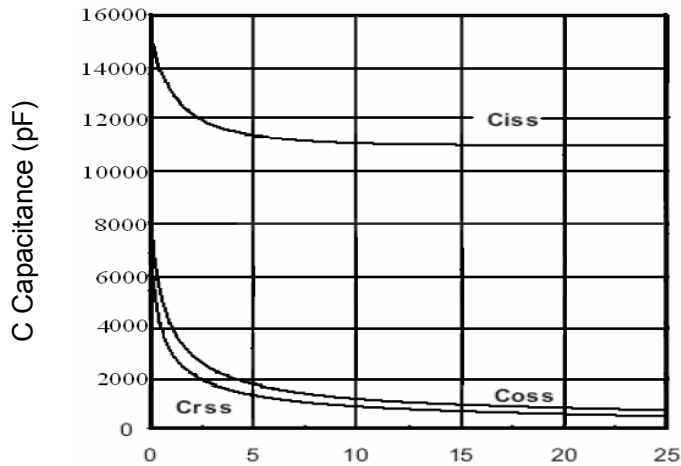
Figure 5 Gate Charge



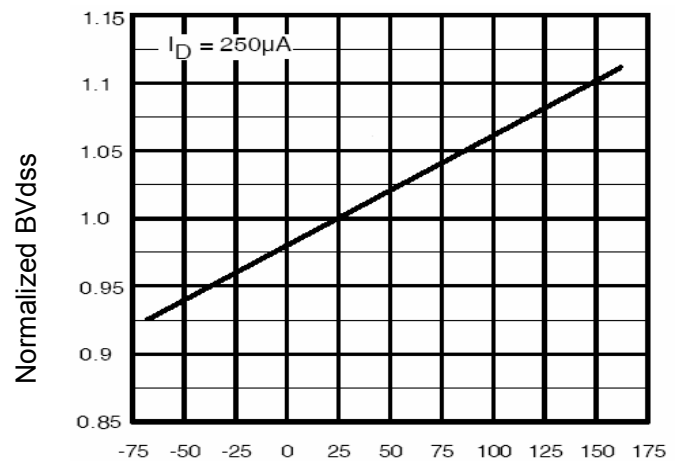
Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

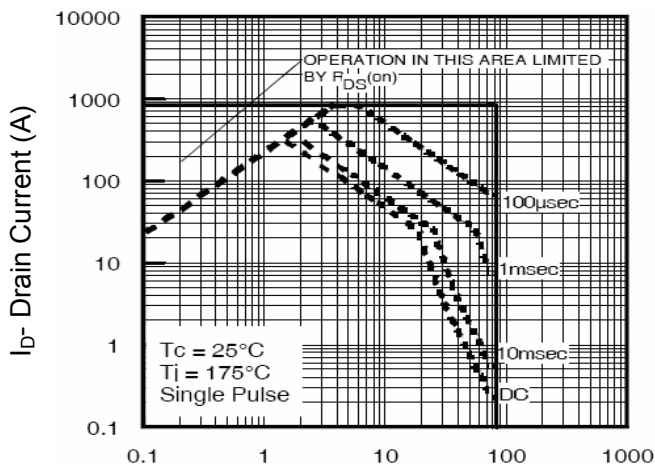
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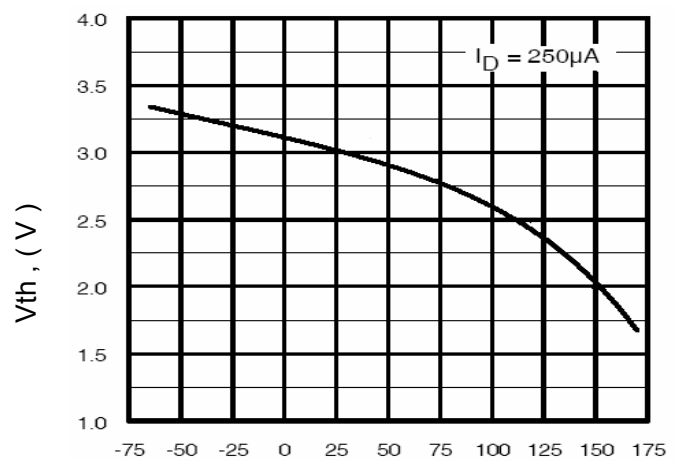
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



TJ-Junction Temperature(°C)
Figure 9 BV_{DSS} vs Junction Temperature



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



TJ-Junction Temperature(°C)
Figure 10 V_{GS(th)} vs Junction Temperature

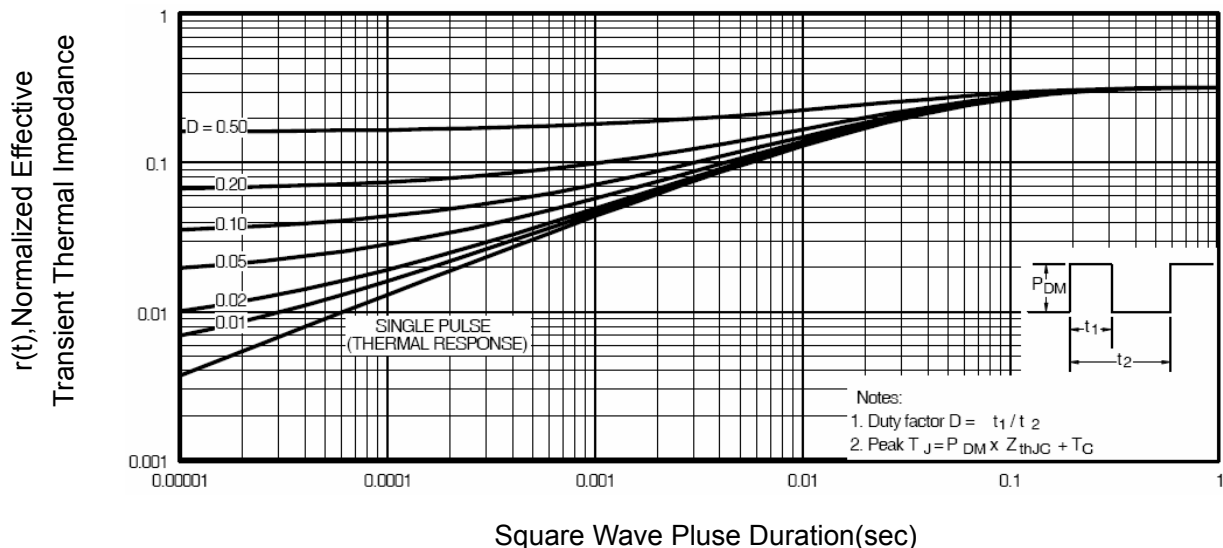
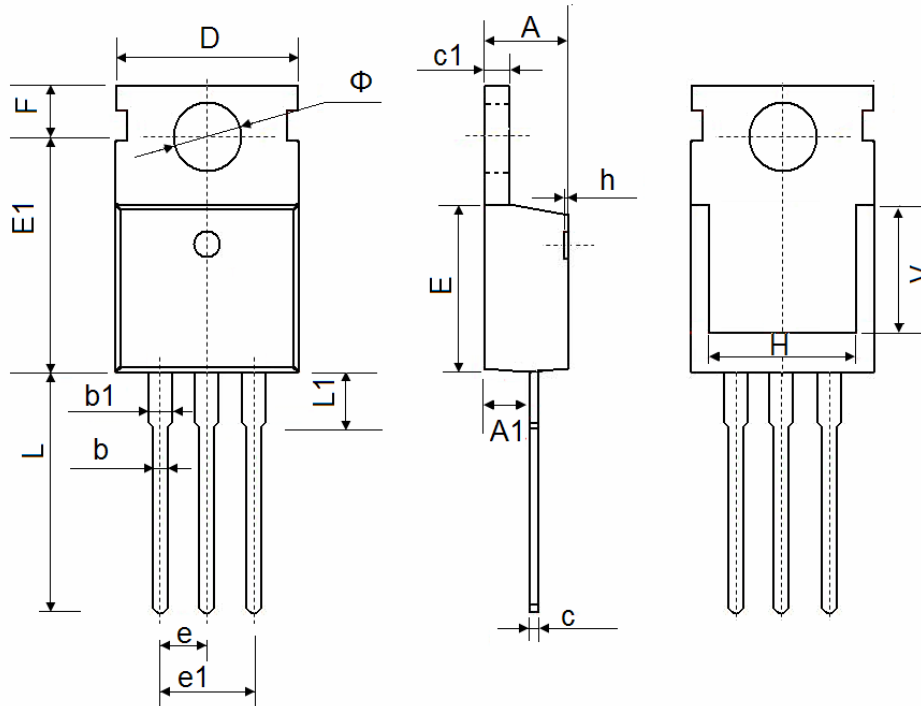


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information
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Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150